

What is claimed is:

1. A production process for a semiconductor device having a metal electrode provided on a semiconductor substrate thereof, the semiconductor device production process comprising the steps of:

forming a metal electrode portion on a surface of another substrate for electrode transfer; and

transferring the metal electrode portion from the electrode transfer substrate onto the semiconductor substrate by pressing together the electrode transfer substrate and the semiconductor substrate.

2. A semiconductor device production process as set forth in claim 1,

wherein the electrode transfer substrate has a seed film provided on the surface thereof,

wherein the step of forming the metal electrode portion on the electrode transfer substrate includes the step of depositing a material for the metal electrode on the seed film by plating.

20 3. A semiconductor device production process as set forth in claim 2,

wherein the electrode transfer substrate has a patterning film provided on a surface thereof and partly covering a surface of the seed film to expose a portion 25 of the seed film on which the metal electrode portion

is to be formed.

4. A semiconductor device production process as set forth in claim 3, wherein the patterning film is an insulating film.

5 5. A semiconductor device production process as set forth in claim 2, wherein the seed film is composed of such a material that the metal electrode portion has a lower adhesion affinity for the seed film than for a portion of the semiconductor substrate onto which the metal 10 electrode portion is to be transferred.

6. A semiconductor device production process as set forth in claim 2,

wherein the electrode transfer substrate is composed of a transparent material,

15 wherein the seed film is locally present in a region of the electrode transfer substrate on which the metal electrode portion is to be formed.

7. A semiconductor device production process as set forth in claim 1,

20 wherein a protective film having an opening which exposes therethrough an electrical contact portion of the semiconductor substrate is provided on the semiconductor substrate,

wherein the metal electrode portion is formed in 25 a position on the electrode transfer substrate

corresponding to a position of the electrical contact portion in the step of forming the metal electrode portion on the electrode transfer substrate,

wherein the metal electrode portion is transferred onto the electrical contact portion in the step of transferring the metal electrode portion.